

BRD4N60

Rev.G Apr-2021

描述 / Descriptions

TO-252 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-252 Plastic Package.

特征 / Features

低栅电荷,低反馈电容,开关速度快。无卤产品。

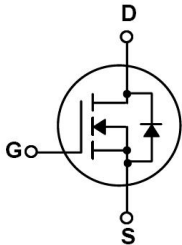
Low gate charge, low crss, fast switching. Halogen-free Product.

用途 / Applications

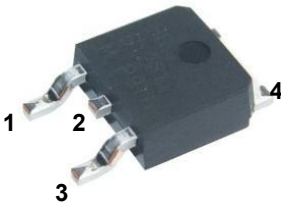
该器件适用于适配器和充电器的功率开关电路

These devices are well suited for power switch circuit of adaptor and charger.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : G

PIN 2 : D

PIN 3 : S

PIN 4 : D

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	4.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	3.2	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	200	mJ
Repetitive Avalanche Energy	E_{AR}	30	mJ
Avalanche Current	I_{AR}	2.5	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	50	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Thermal Resistance Junction-case	R_{thJC}	2.50	$^\circ\text{C/W}$
Thermal Resistance Junction-ambient	R_{thJA}	110	$^\circ\text{C/W}$

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V$ $V_{GS}=0V$			1	μA
		$V_{DS}=480V$ $T_C=125^\circ\text{C}$			100	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$		2.0	2.5	Ω
Forward Transconductance	g_{FS}	$V_{DS}=15V$ $I_D=2.0A$		3.5		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=4.0A$			1.5	V

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		560		pF
Output Capacitance	C_{oss}			45		pF
Reverse Transfer Capacitance	C_{rss}			17		pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=4.0A$ $R_G=25\Omega$		14		ns
Turn-On Rise Time	t_r			13		ns
Turn-Off Delay Time	$t_{d(off)}$			32		ns
Turn-Off Fall Time	t_f			8		ns
Total Gate Charge	Qg	$I_D = 4.0A, V_{DS} = 480V$ $V_{GS} = 10V$		13.3		nC
Gate-to-Source Charge	Qgs			4.1		nC
Gate-to-Drain Charge	Qgd			2.8		nC
Continuous Diode Forward Current	I_S				4.0	A
Reverse Recovery Time	t_{rr}	$T_j=25^\circ C, I_f=4.0A$		390		nS
Reverse Recovery Charge	Qrr	$di/dt=100A/\mu s$		1.5		uC

电参数曲线图 / Electrical Characteristic Curve

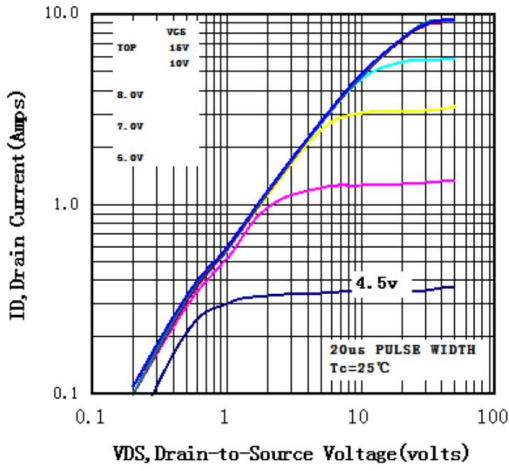


Fig1 Typical Output Characteristics, $T_c=25^\circ\text{C}$

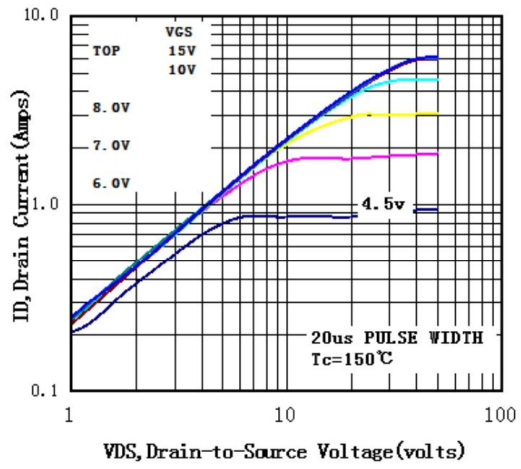


Fig2 Typical Output Characteristics, $T_c=150^\circ\text{C}$

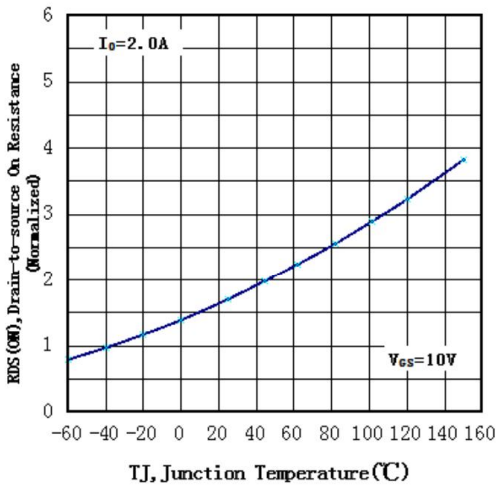


Fig3 Normalized Resistance Vs. Temperature

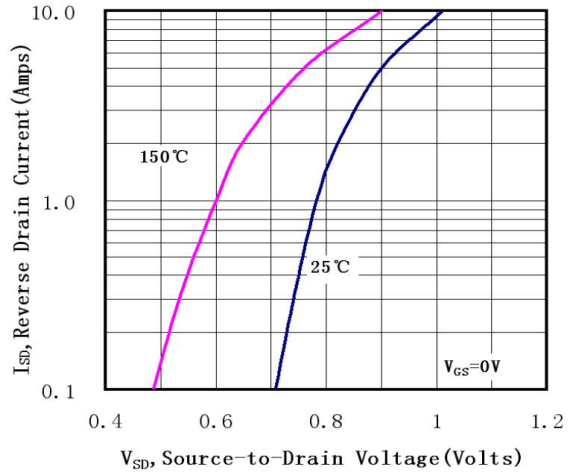


Fig4 Typical Source-Drain Diode Forward Voltage

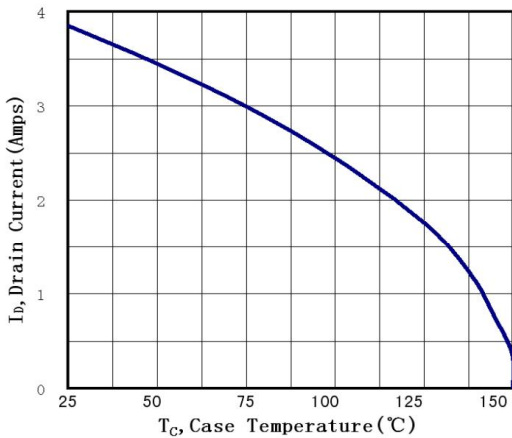


Fig5 Maximum Drain Current Vs. Case Temperature

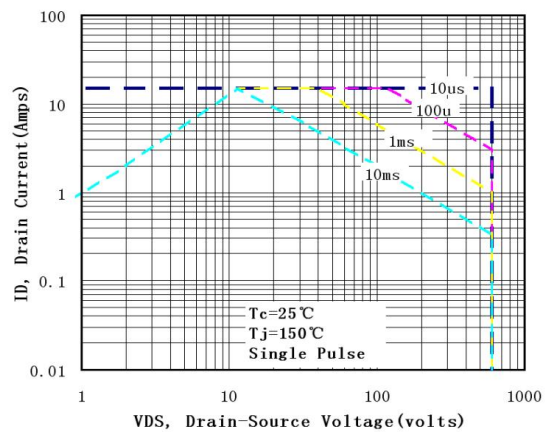
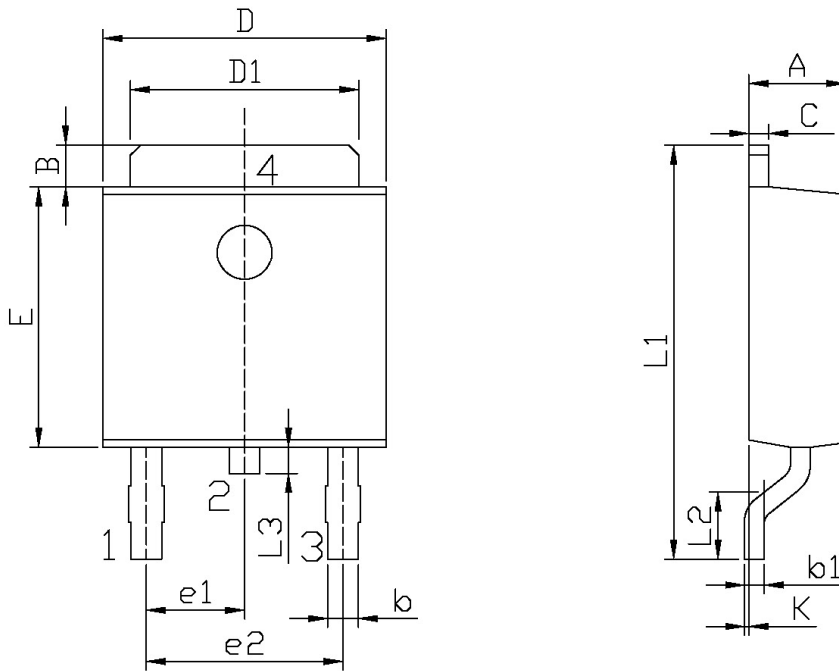


Fig6 Maximum Safe Operating Area

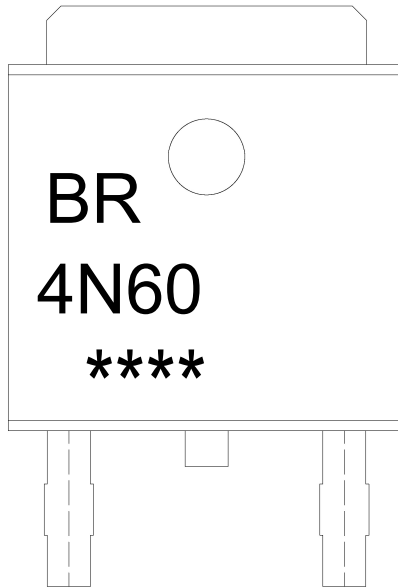
外形尺寸图 / Package Dimensions



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252



说明：

BR： 为公司代码

4N60： 为型号代码

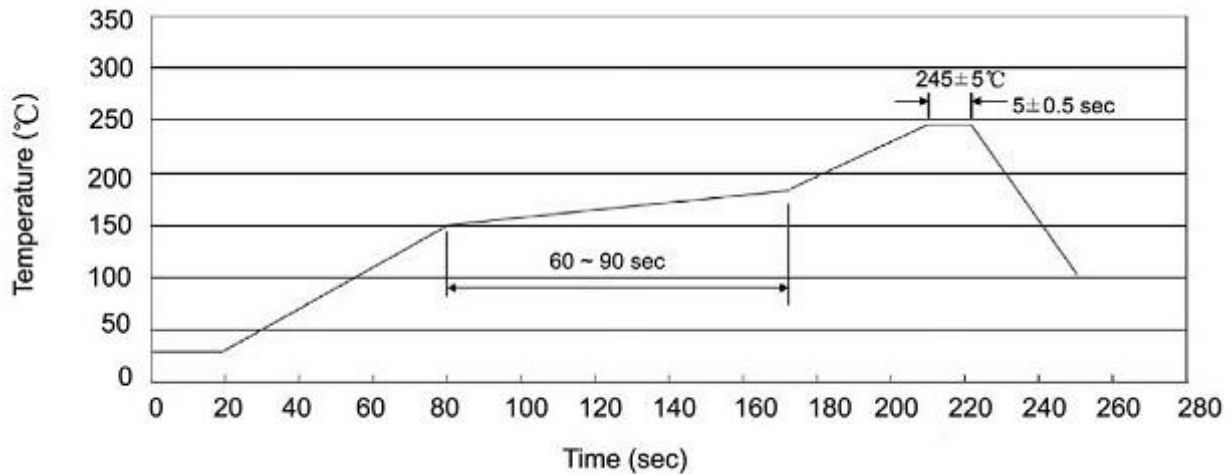
****： 为生产批号代码，随生产批号变化。

Note:

BR: CompanyCode

4N60: Product Type.

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150 ~ 180°C，时间 60 ~ 90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
- 3.Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	5	25,000	13" ×16	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

使用说明 / Notices